PCN Number:	20171129000	**PCN Date:**	Nov 30, 2017
Title:	Qualification of CFAB as an additional wafer fab site option for select devices in LBC5 process technology		
Customer Contact:	PCN Manager	**Dept:**	Quality Services
Proposed 1st Ship Date:	Mar 1, 2018	**Estimated Sample Availability:**	Date provided at sample request.
Change Type:			

☐	Assembly Site	☐	Assembly Process	☐	Assembly Materials
☐	Design	☐	Electrical Specification	☐	Mechanical Specification
☐	Test Site	☐	Packing/Shipping/Labeling	☐	Test Process
☐	Wafer Bump Site	☐	Wafer Bump Material	☐	Wafer Bump Process
☒	Wafer Fab Site	☐	Wafer Fab Materials	☐	Wafer Fab Process
		☐	Part number change		

PCN Details

Description of Change:

This change notification is to announce the qualification of CFAB as an additional wafer fab site option for the LBC5 devices listed in the product affected section of this document.

Current			Additional		
Current Fab Site	**Process**	**Wafer Diameter**	**Additional Fab Site**	**Process**	**Wafer Diameter**
DP1DM5	LBC5	200 mm	CFAB	LBC5	200 mm

The LBC5 process technology has been running successfully in production at CFAB since 2012.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current

Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas

New

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
CFAB	**CU3**	**CHN**	Chengdu

Sample product shipping label (not actual product label)

Product Affected:		
TPA3250D2DDW	TPA3250D2DDWR	

Qualification Report

Qualification of LBC5 Process Technology at CFAB
Approved 03/02/2012

Die Attributes

Attributes	Process QBS : TAS5613APHD Approved: 3/2/2012	Process QBS: DRV8813A0PWP Approved: 3/2/2012	Process QBS: SN8C0183PWP Approved: 3/2/2012
Wafer Fab Site	CFAB	CFAB	CFAB
Wafer Fab Process	LBC5	LBC5	LBC5
Wafer Diameter	200mm	200mm	200mm

- QBS: Qual By Similarity
- Qual Device TAS5613APHD and SN8C0183PWP are qualified at LEVEL3-260C
- Qual Device DRV8813A0PWP is qualified at LEVEL1-260C

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TAS5613APHD	Qual Device: DRV8813A0PWP	Qual Device: SN8C0183PWP
AC	Autoclave 121C	96 Hours	3/77/0	3/77/0	-
ED	Electrical Characterization	Per Datasheet Parameters	3/Pass	3/Pass	3/3/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/77/0	-	-
HBM	ESD - HBM	1500 V	3/21/0	1/3/0	-
CDM	ESD - CDM	250 V	3/15/0	1/3/0	-
HTOL	Life Test, 155C	240 Hours	3/77/0		3/77/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/77/0	-	-
LU	Latch-up	(per JESD78)	3/6/0	1/6/0	-
TC	Temperature Cycle, -65/150C	500 Cycles	3/77/0	3/77/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
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